

Fig. 1

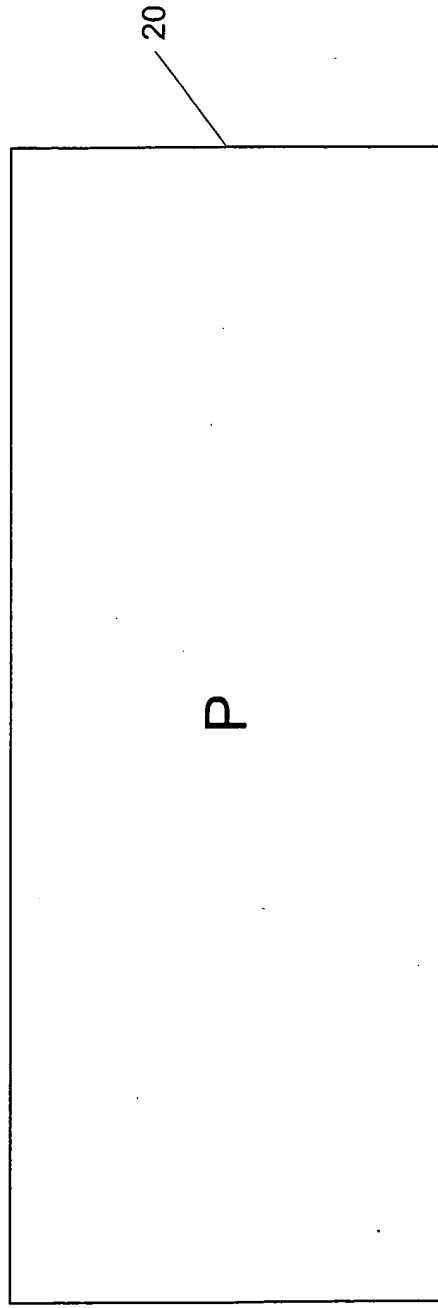


Fig. 2a

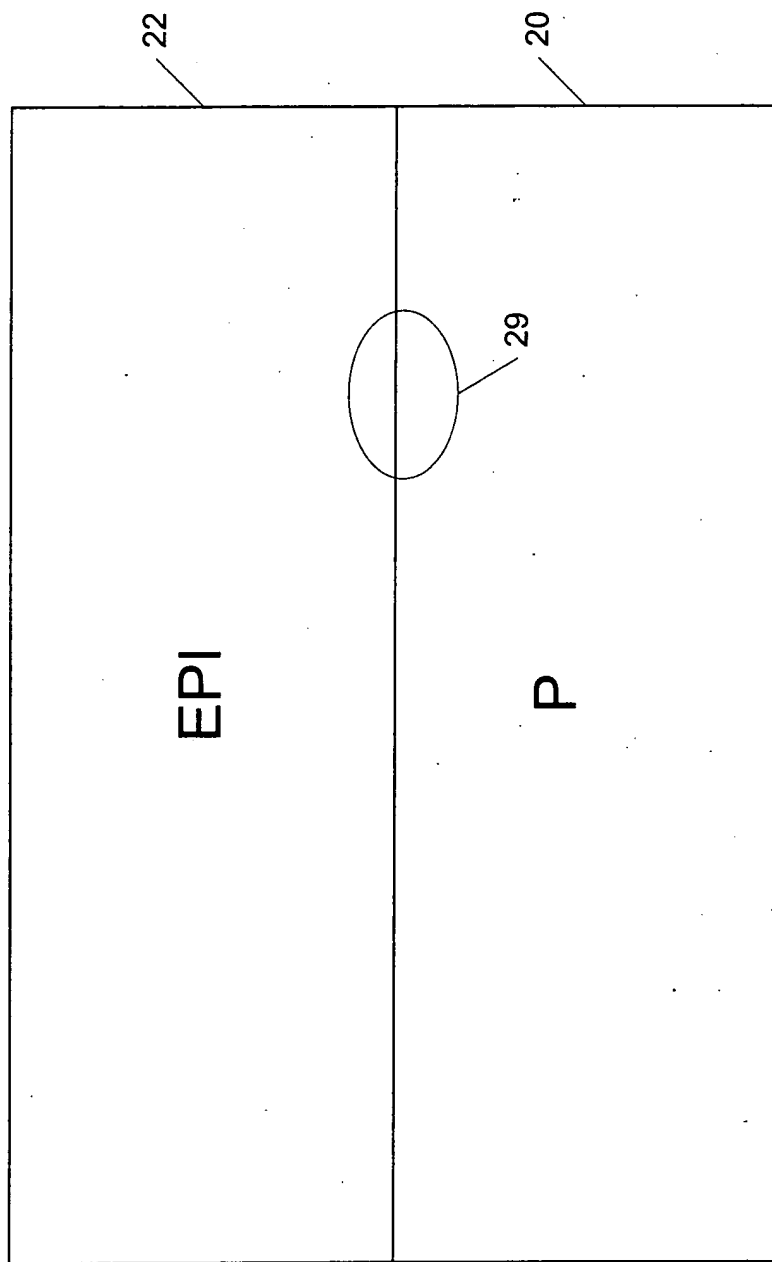


Fig. 2b

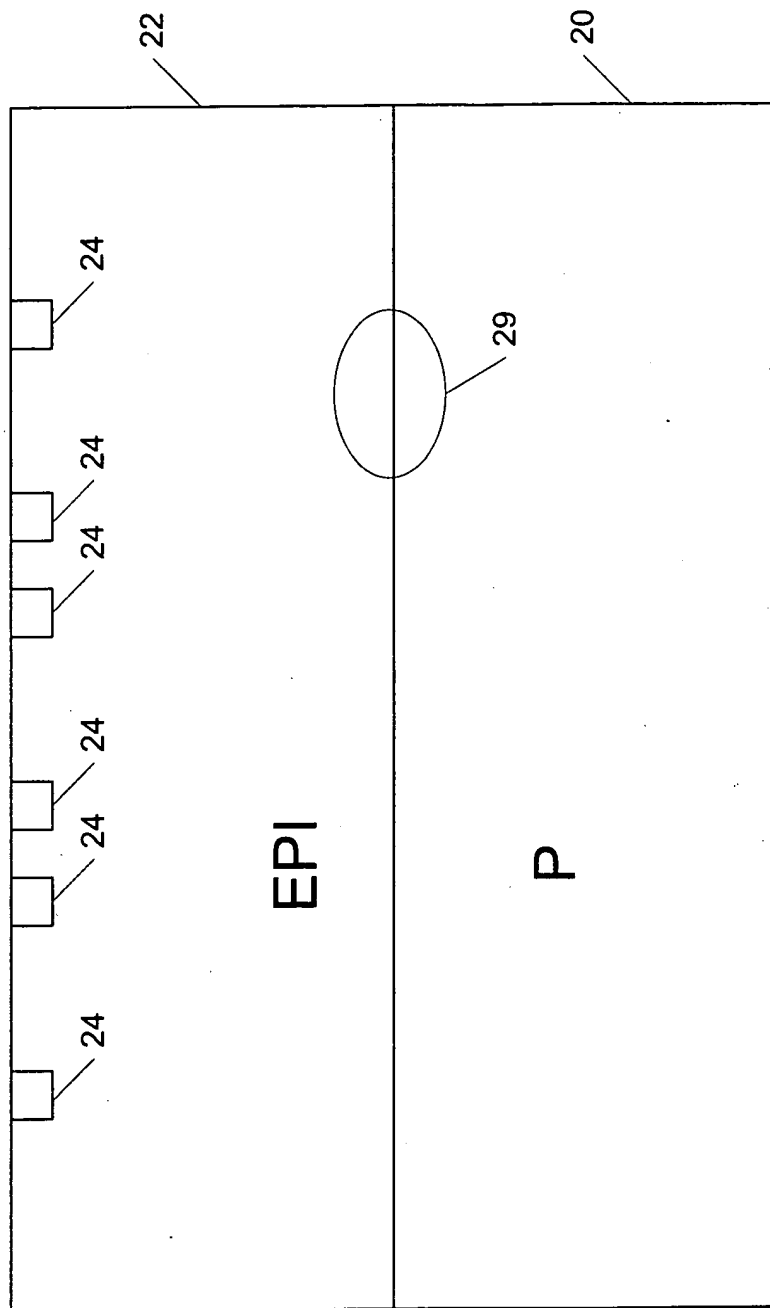


Fig. 2c

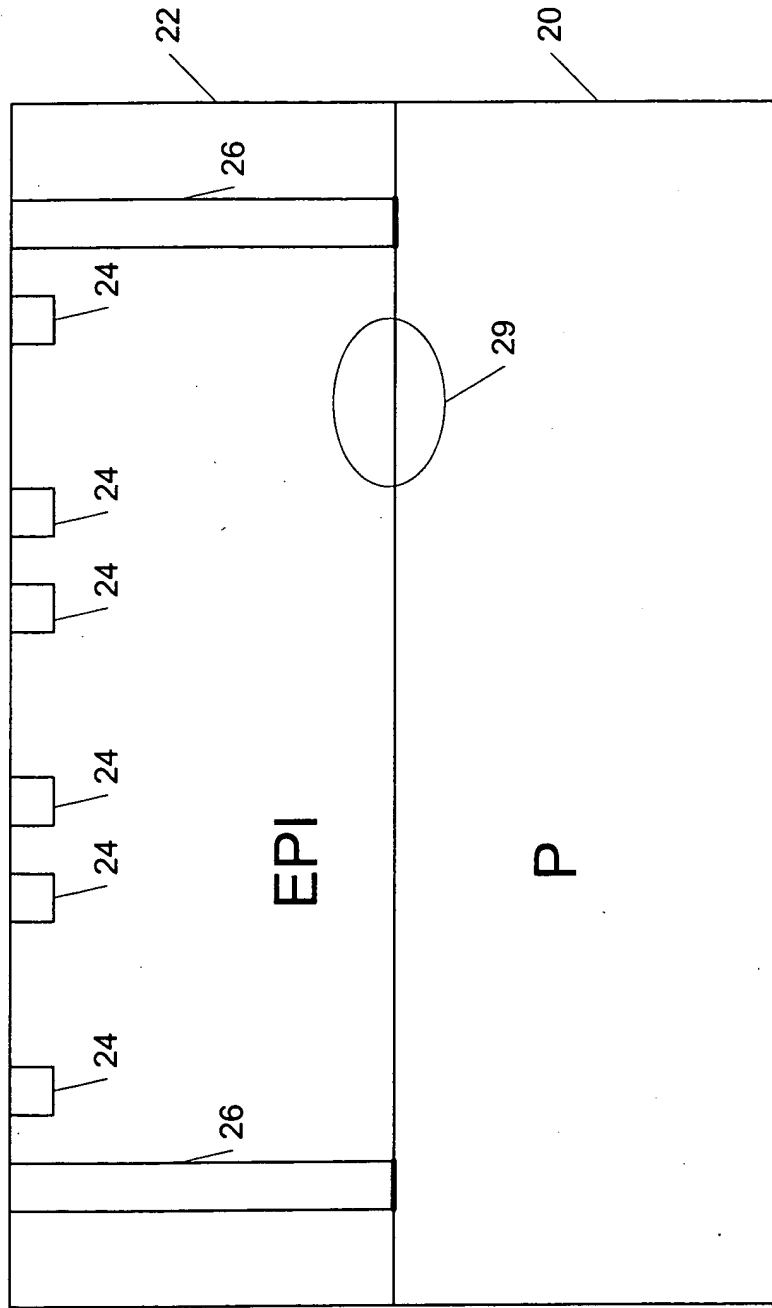


Fig. 2d

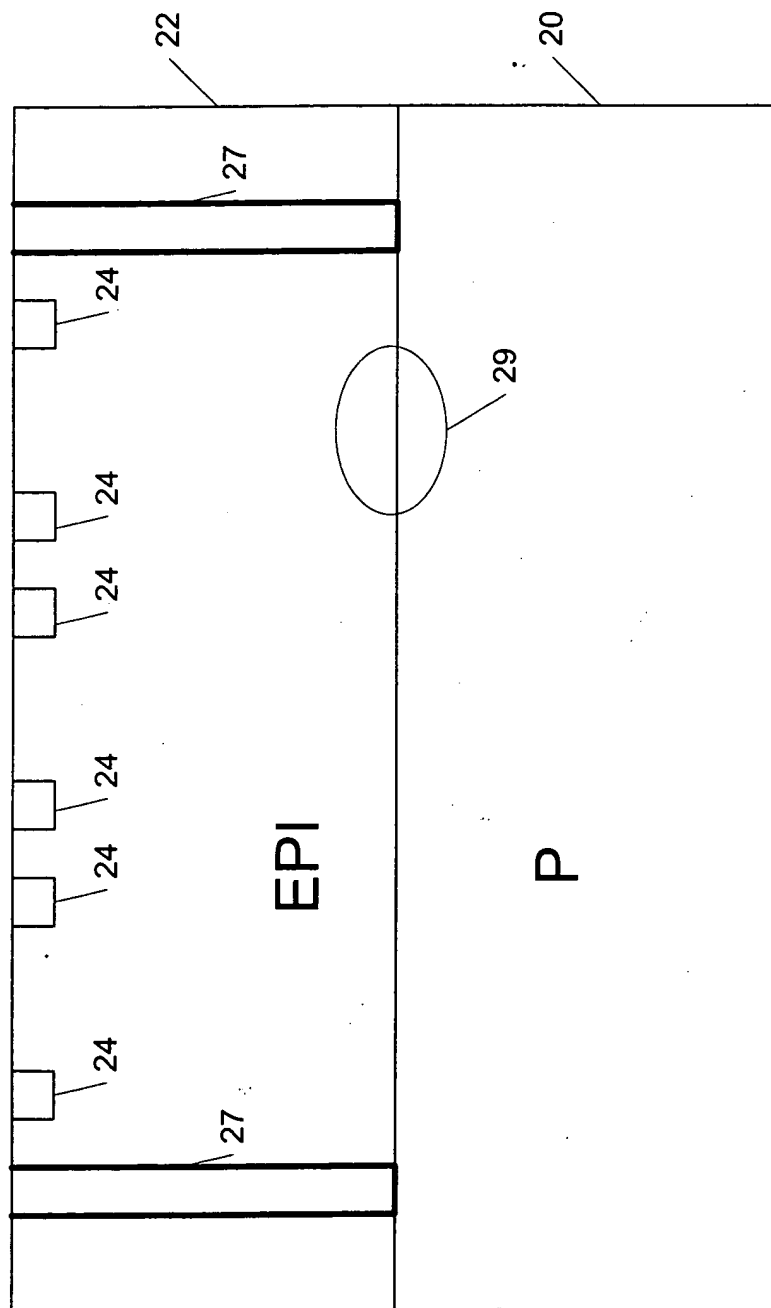


Fig. 2e

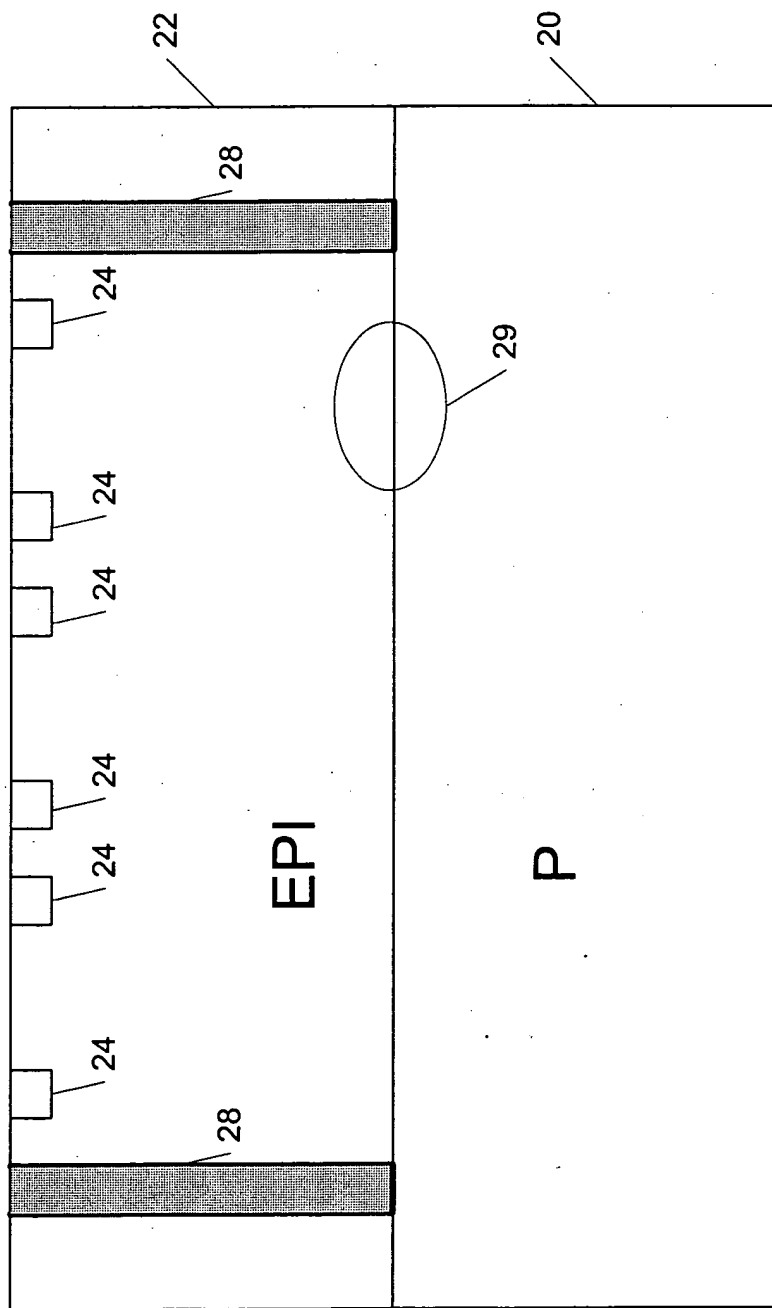


Fig. 2f

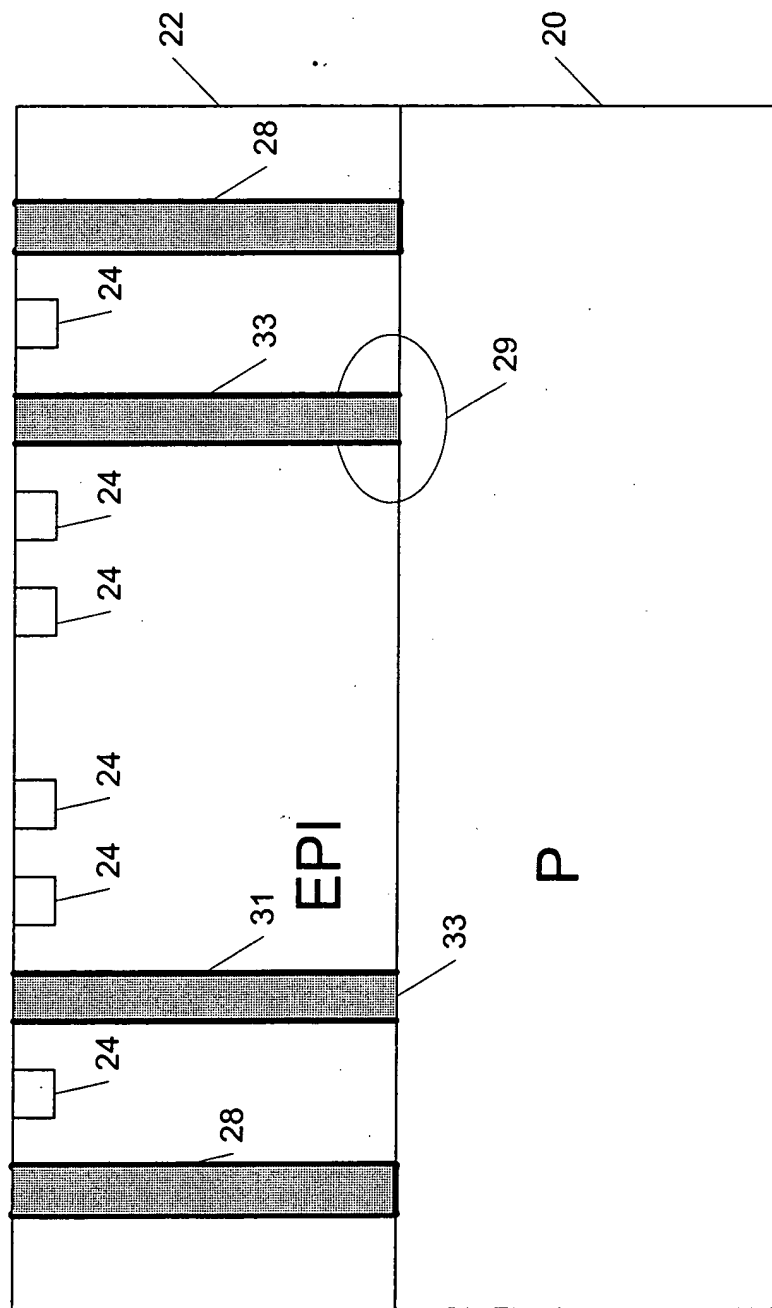


Fig. 2g



10034279 122801

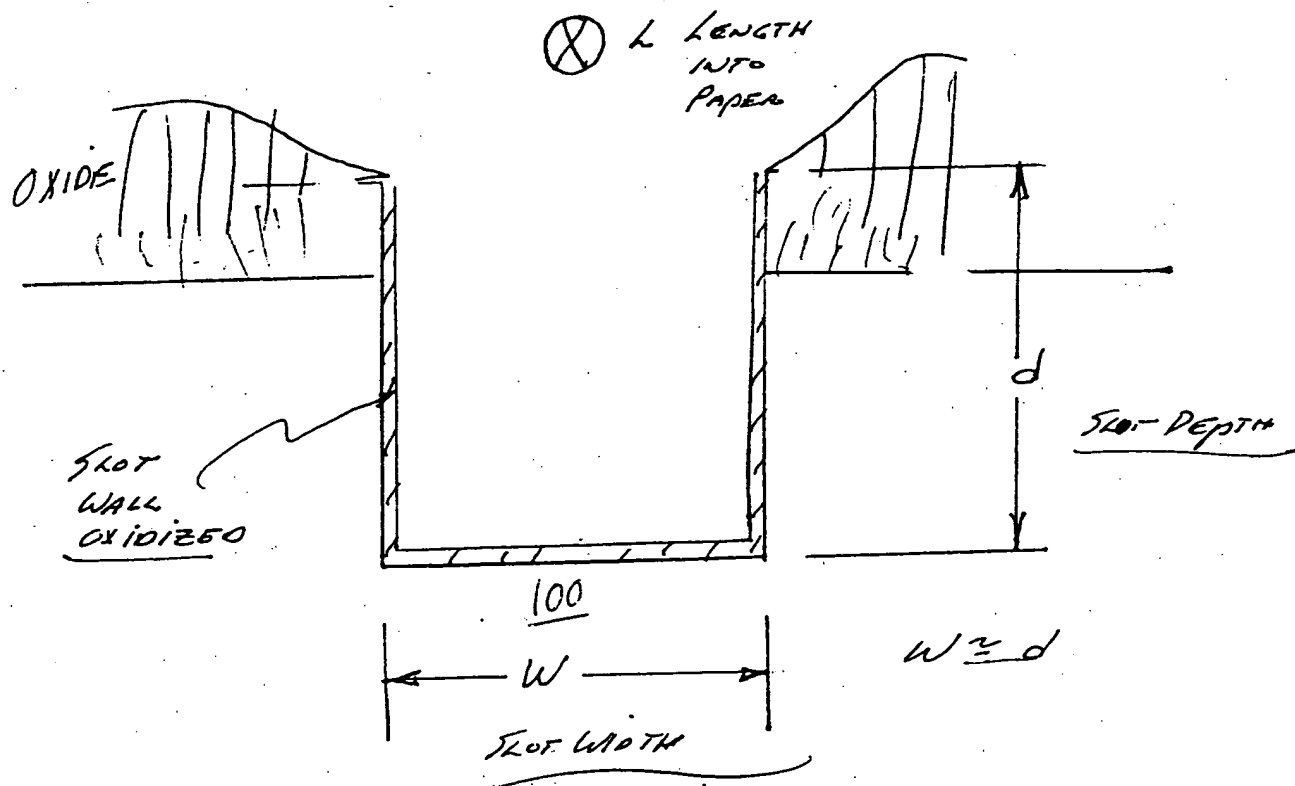


Fig. 3

10034279-122801

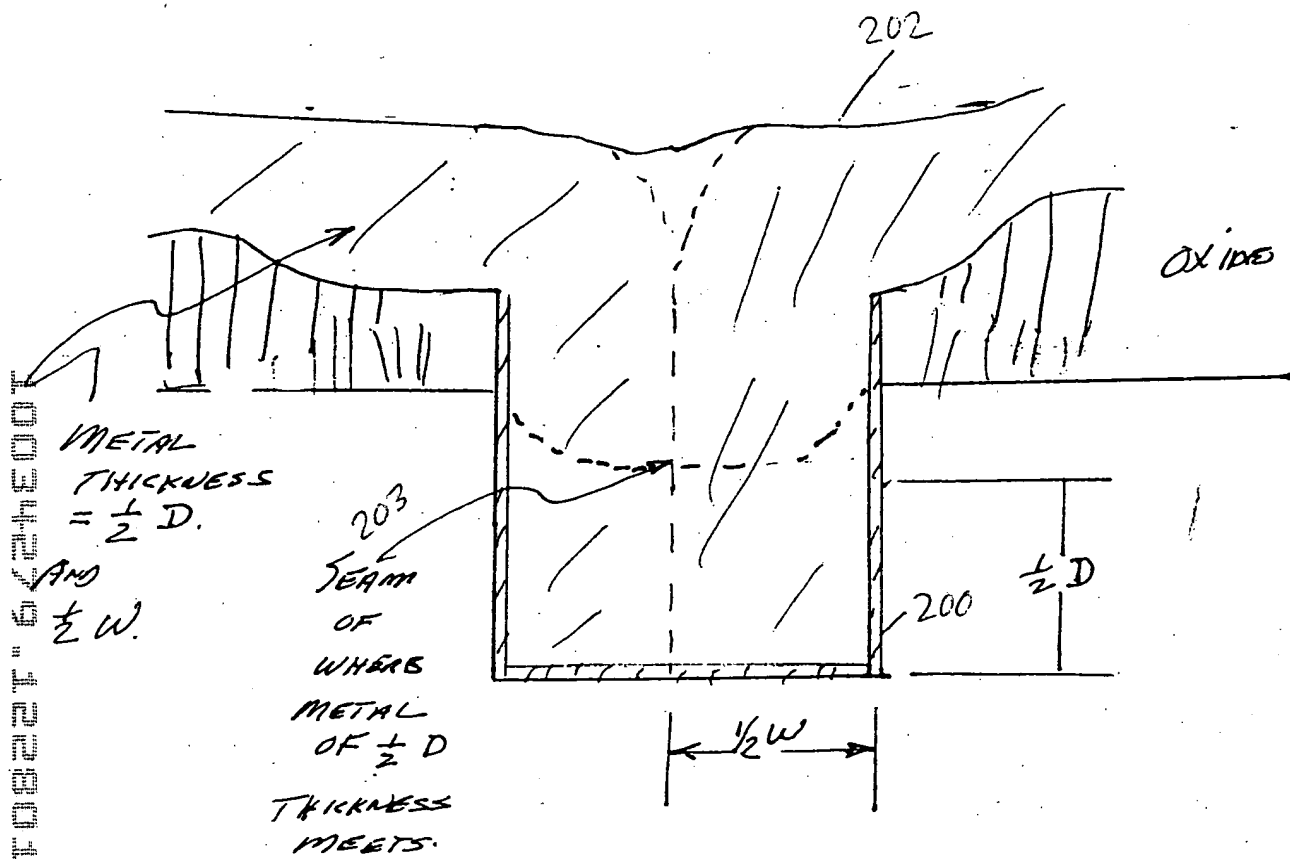
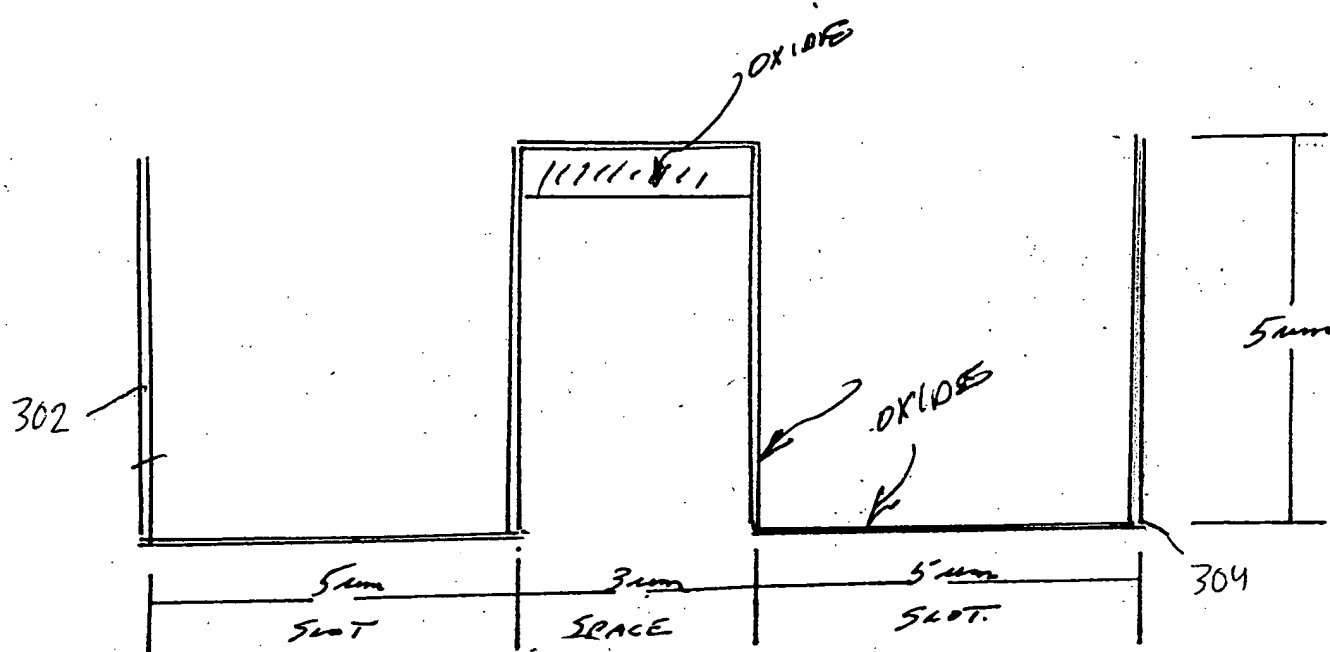


Fig. 4

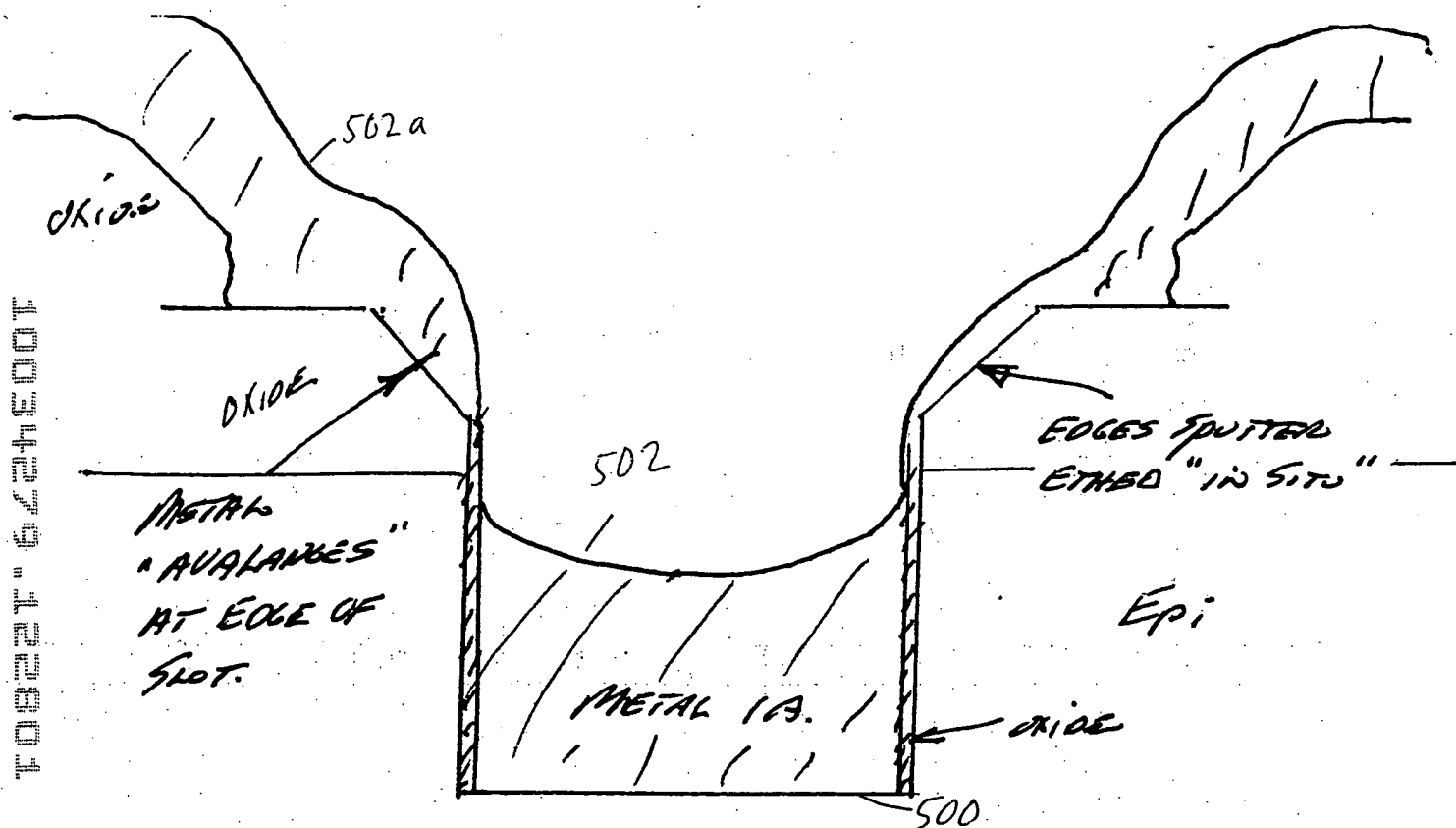
10034279-122801



DOUBLE SLOT FOR  
DOUBLE WIDTH OF METAL.  
3mm SPACE BETWEEN SLOTS

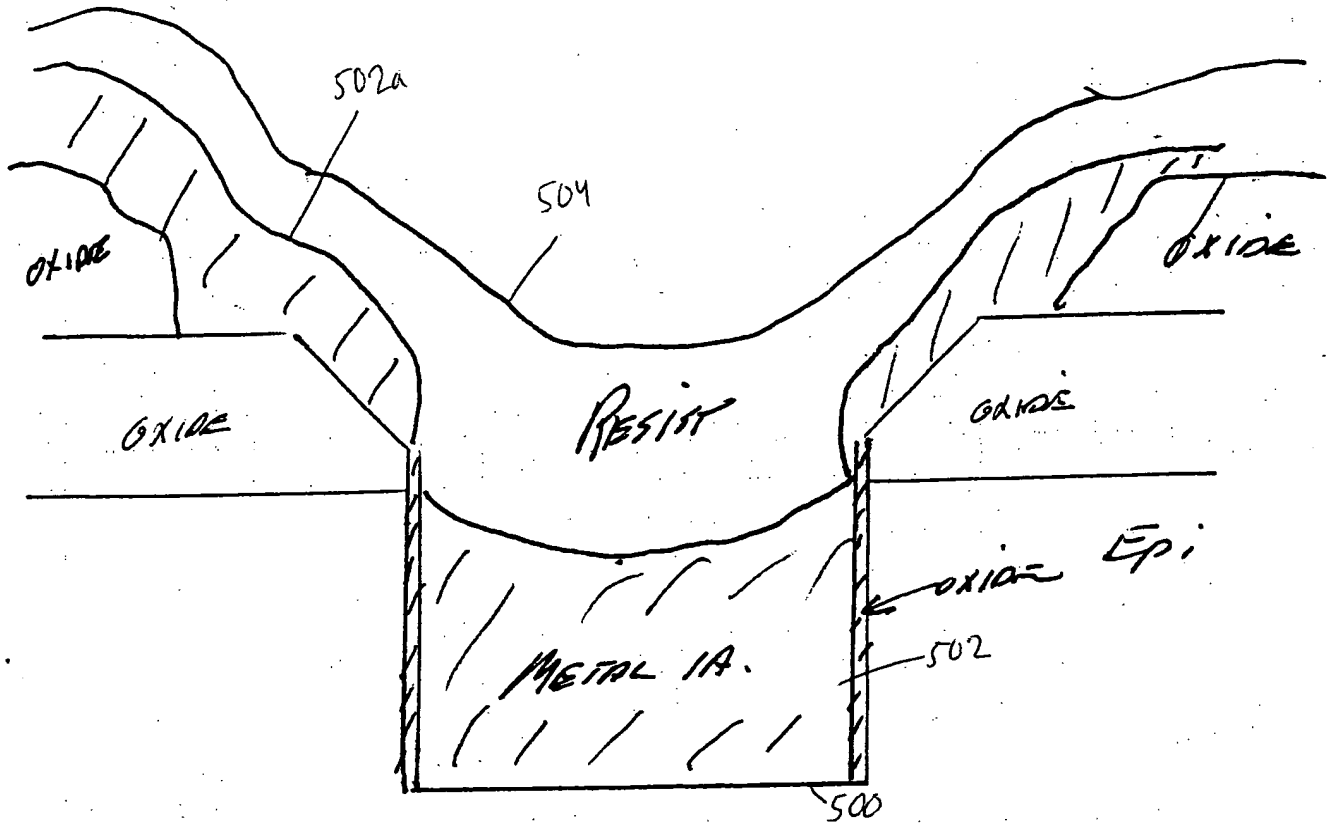
Fig. 4a

10034279-122801



Prior TO METAL 1A BEING  
SPUTTERED, THE EDGES OF THE OXIDES  
ARE SPUTTERED ETCHED "IN SITU" &  
1A DEPOSITED

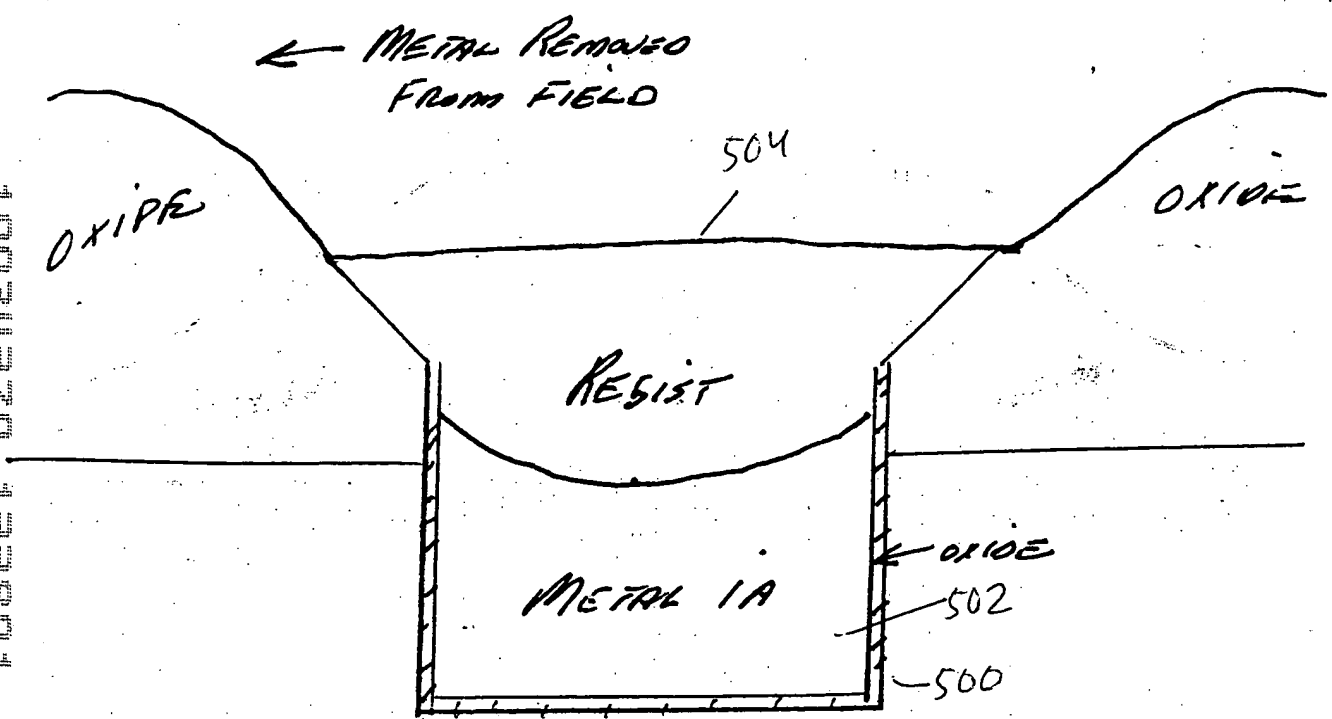
Fig. 5



RESIST COATING - THICK IN THE  
SLOTS

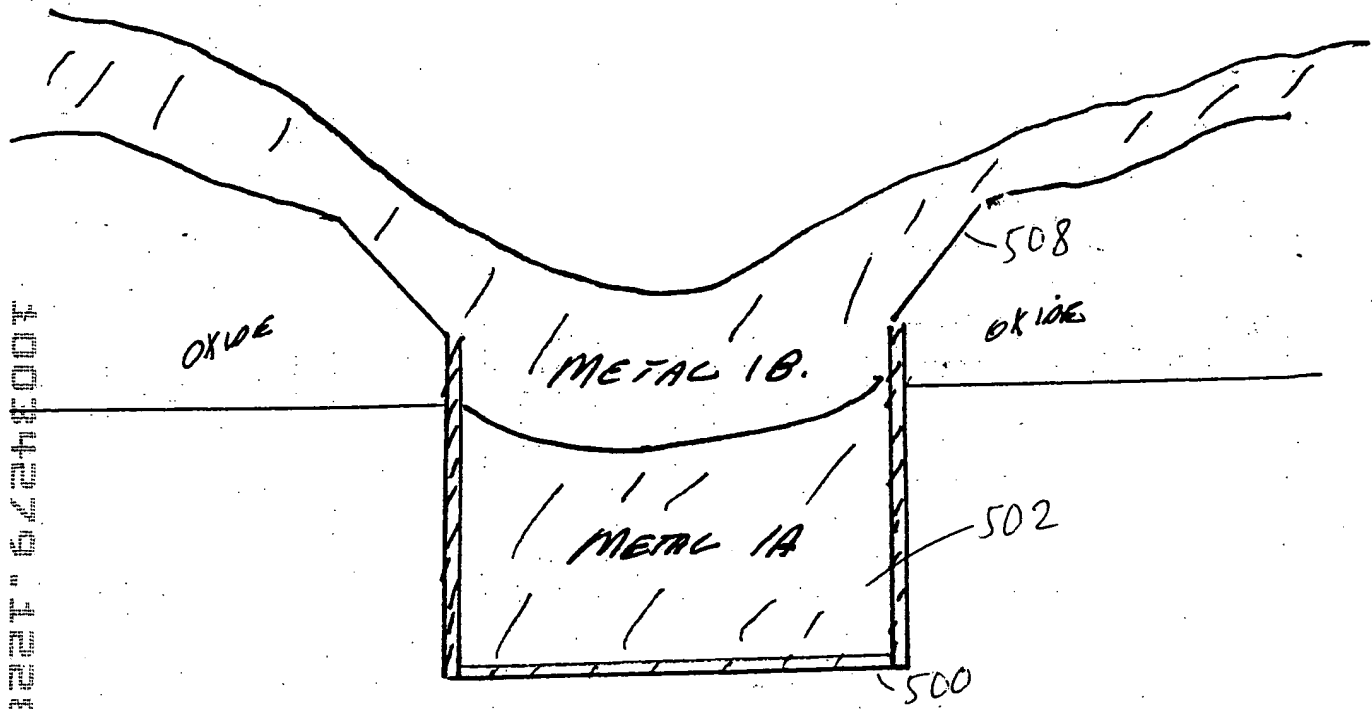
Fig. 6

10034279 123801  
FOOT SHEET



RESIST PLANNED ETCHED.  
LEAVING RESIST IN SLITS  
FIELD METAL ETCHED OFF.

Fig. 7



RESIST STRIPPED & SECOND  
METAL 1B SPUTTER DEPOSITED

Fig. 8

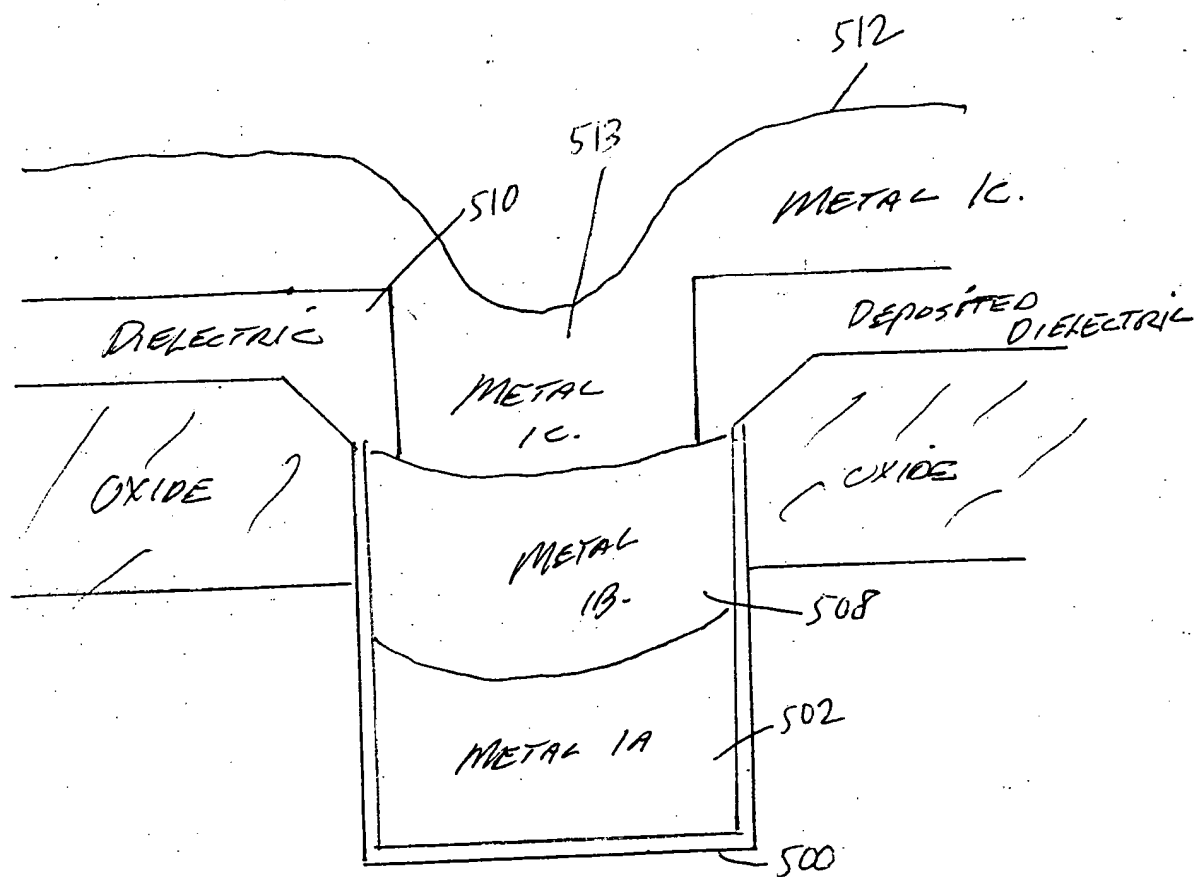


Fig. 9



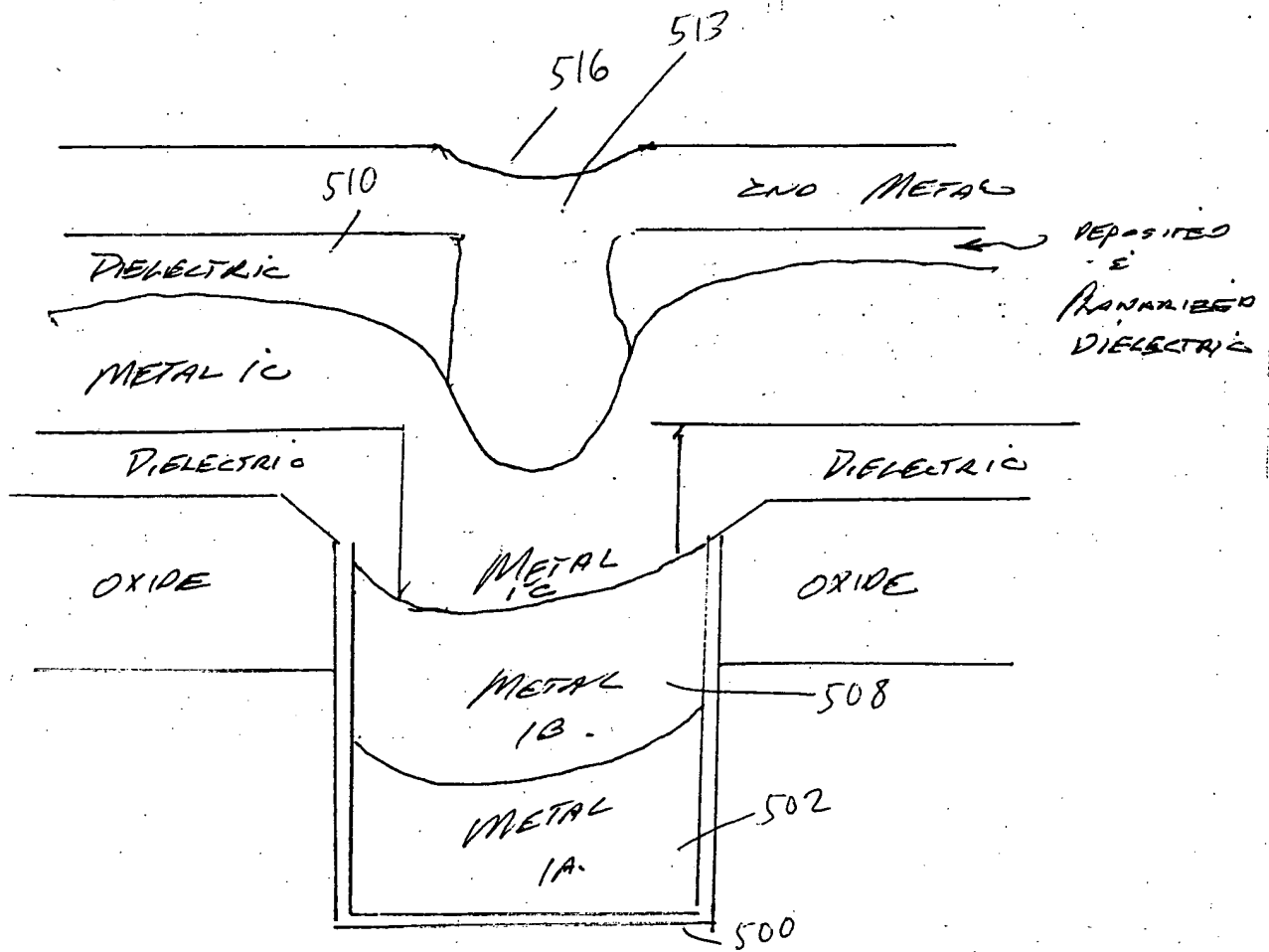
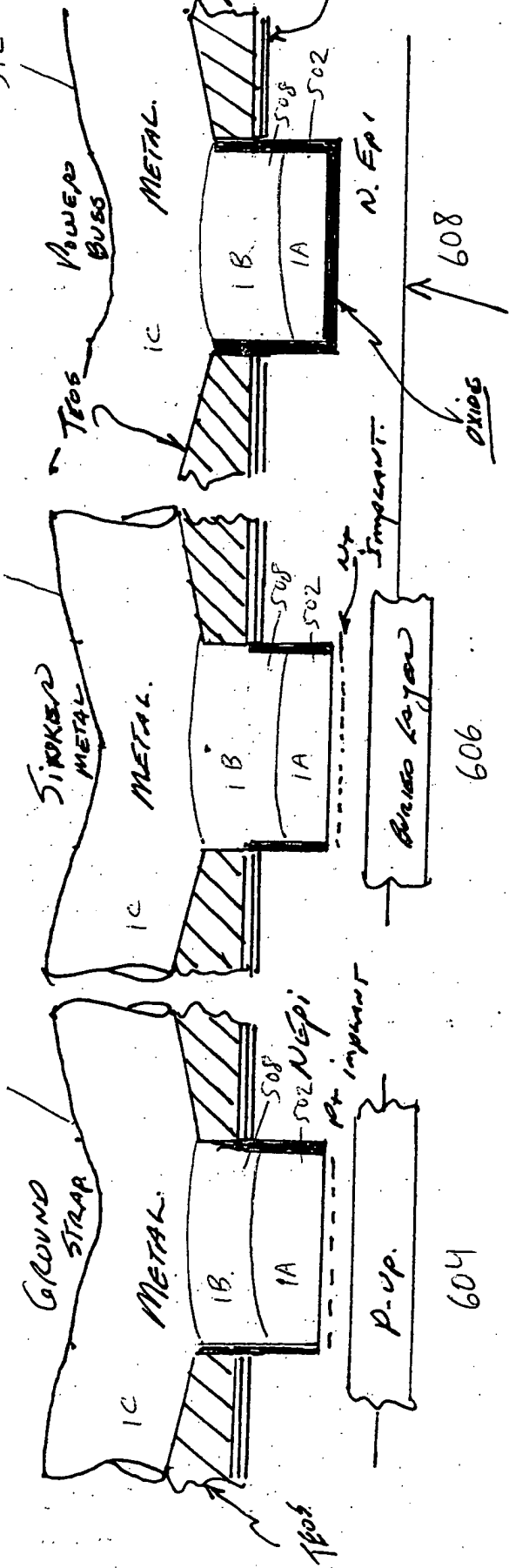


Fig. 10



Ground Strap

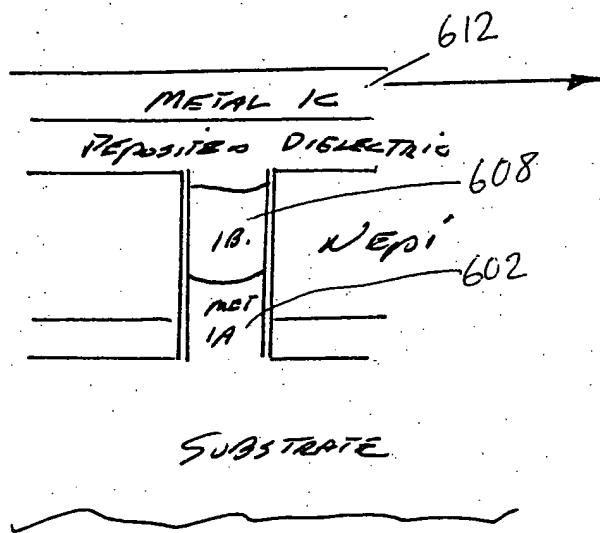
Drain/Buried Layer / Not Impur

Power Buss

Ground Strap / Power Buss / Drain Metal Sinker

Thin outer layer of DIELECTRIC  
 FOLLOWED BY 9000 Å TEOS - POLISH -  
 THIN MASS - METAL.  
 METAL 15-20 nm deposited

Fig. 11 Power Metal.



METAL IC  
 CONNECTS AN ISOLATED  
 ISLAND TO ADJACENT  
 ISOLATED EPI ISLANDS  
 AND CROSSES OVER THE  
 ISOLATION GROUND  
 STRAP BY NOT OPENING  
 A VIA IN THIS PORTION  
 TO ALLOW IC TO BE  
 ISOLATED FROM GROUND.

Fig. 12